

### AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

#### **Listing of Claims:**

1. (Currently Amended) A mask for a nanoprint lithographic process, comprising:  
a translucent material that transfers pattern from the mask to a substrate when placed in physical contact with the substrate or when placed against the substrate with a predetermined pressure applied there between;  
one or more three-dimensional features comprising one or more vertical sidewalls;  
an absorbing material deposited upon one or more of the vertical sidewalls so that light ~~in~~ an incident direction to on an upper surface of the substrate will be absorbed by the absorbing material, resulting in light blocking features such that upon the transfer of the pattern, the substrate comprises features which directly correspond to areas of the absorbing material deposited on the vertical sidewalls; and  
one or more horizontal surfaces, formed upon one or more of the three-dimensional features, that allow light rays to exit a lower surface of the substrate unobstructed by the absorbing material.
2. (Currently Amended) The mask of claim 1, the translucent ~~substrate~~ material comprising silicon dioxide.
3. (Currently Amended) The mask of claim 1, the translucent ~~substrate~~ material being quartz.
4. (Original) The mask of claim 1, the absorbing material comprising SiON.
5. (Original) The mask of claim 1, the absorbing material comprising Si – rich nitride.

6. (Original) The mask of claim 1, the absorbing material comprising Si – rich oxide.
7. (Original) The mask of claim 1, the absorbing material comprising SiOCN.
8. (Original) The mask of claim 1, the absorbing material comprising TiN.

9-23 (Canceled)